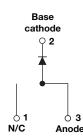
VS-HFA25TB60S-M3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 25 A



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PRIMARY CHARACTERISTICS					
I _{F(AV)} 25 A					
V _R	600 V				
V _F at I _F	1.3 V				
t _{rr} (typ.)	23 ns				
T _J max.	150 °C				
Package	D ² PAK (TO-263AB)				
Circuit configuration	Single				

FEATURES

- Ultrafast and ultrasoft recovery
- \bullet Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA25TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		600	V			
Maximum continuous forward current	١ _F	T _C = 100 °C	25				
Single pulse forward current	I _{FSM}		225	А			
Maximum repetitive forward current	I _{FRM}		100				
Maximum power dissignation	PD	T _C = 25 °C	125	W			
Maximum power dissipation		T _C = 100 °C	50	vv			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

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COMPLIANT HALOGEN

FREE

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
Maximum forward voltage		I _F = 25 A	See fig. 1	-	1.3	1.7	V
	V _{FM}	I _F = 50 A		-	1.5	2.0	
		I _F = 25 A, T _J = 125 °C		-	1.3	1.7	
Maximum reverse	1	$V_{R} = V_{R}$ rated	See fig. 2	-	1.5	20	
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See lig. 2	-	600	2000	μA
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	55	100	pF
Series inductance	L _S	Measured lead to lead 5 mm from pa	ackage body	-	8.0	-	nH

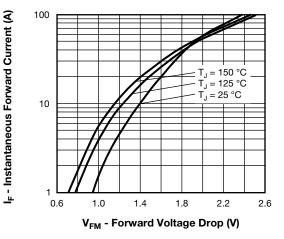
DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	I _F = 1.0 A, dI _F /dt = 200	A/ μ s, V _R = 30 V	-	23	-		
Reverse recovery time See fig. 5	t _{rr1}	T _J = 25 °C		-	50	75	ns	
000 lig. 0	t _{rr2}	T _J = 125 °C	I _F = 25 A	-	105	160	1	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	10	A	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.0	15		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	dI _F /dt = 200 A/µs V _B = 200 V	-	112	375	nC	
See fig. 7	Q _{rr2}	T _J = 125 °C	v _R = 200 v	-	420	1200		
Peak rate of fall recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	250	-		
	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	A∕µs	

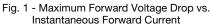
THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	Tlead	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.0	K/W		
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	80	r∧ vv		
Weight			-	2.0	-	g		
weight			-	0.07	-	oz.		
Marking device		Case style D ² PAK (TO-263AB)		HFA2	TB60S			



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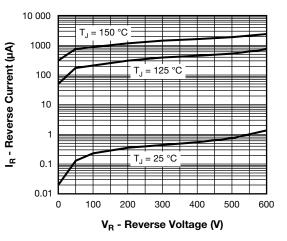


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

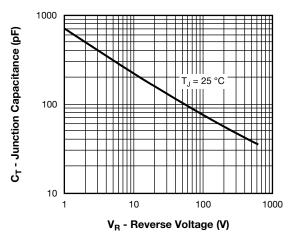
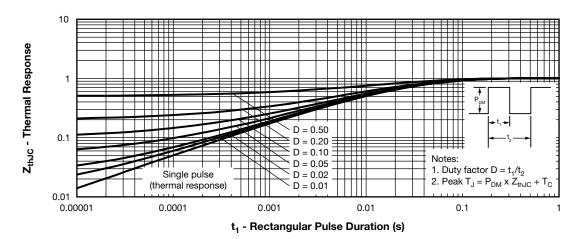


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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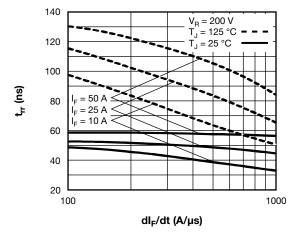
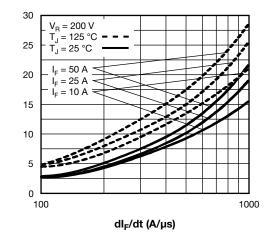


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt



I_{rr} (A)

Fig. 6 - Typical Recovery Current vs. dl_F/dt

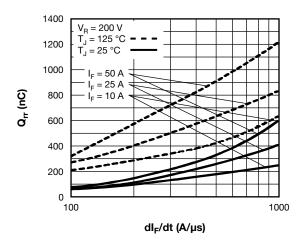


Fig. 7 - Typical Stored Charge vs. dl_F/dt



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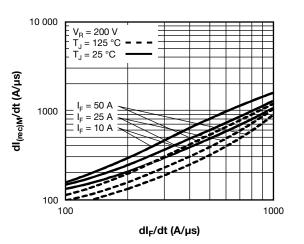


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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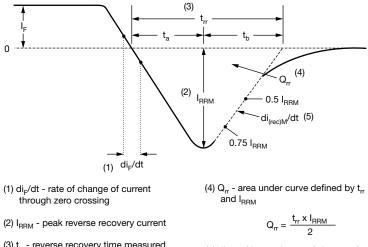
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(3) $t_{rr}^{}$ - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

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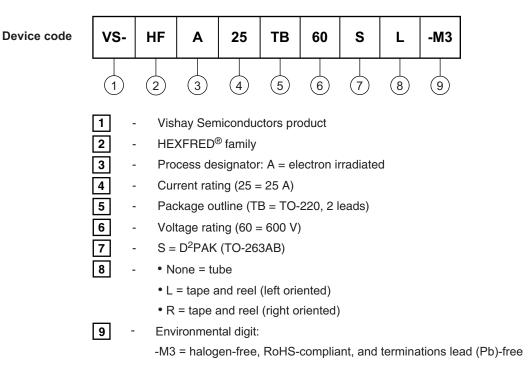
(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

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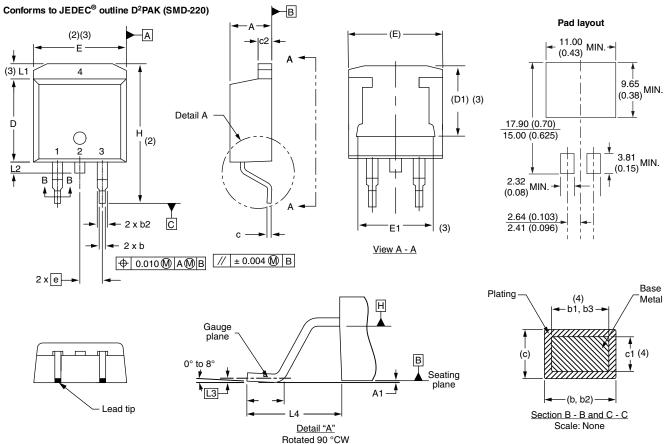
ORDERING INFORMATION (Example)							
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPT							
VS-HFA25TB60S-M3	50	Antistatic plastic tube					
VS-HFA25TB60SR-M3	800	13" diameter reel					
VS-HFA25TB60SL-M3	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				

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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INCHES		NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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